



HIGH DENSITY MOUNTING PHOTOTRANSISTOR OPTICALLY COUPLED ISOLATORS

DESCRIPTION

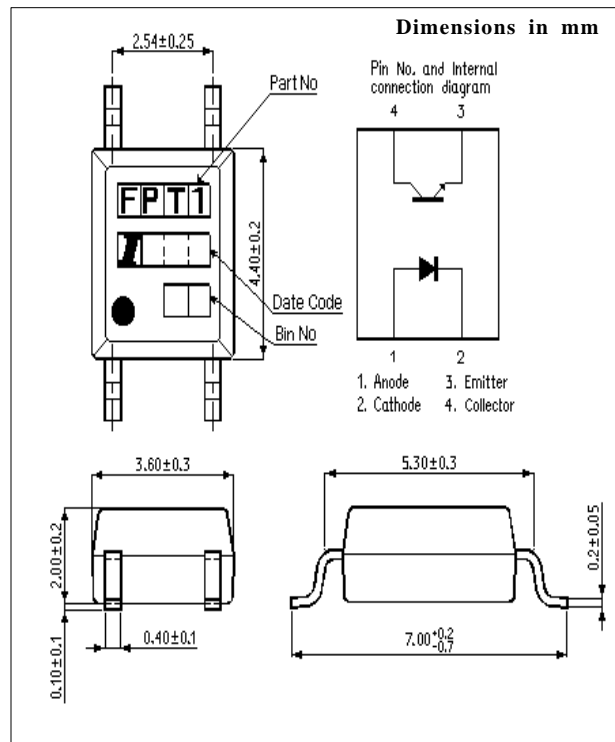
The IS357 is an optically coupled isolator consisting of an infrared light emitting diode and NPN silicon photo transistor in a space efficient dual in line plastic package.

FEATURES

- Marked as FPT1.
- Current Transfer Ratio MIN. 50%
- Isolation Voltage (3.75kV_{RMS}, 5.3kV_{PK})
- All electrical parameters 100% tested
- Drop in replacement for Sharp PC357

APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Measuring instruments
- Signal transmission between systems of different potentials and impedances



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ABSOLUTE MAXIMUM RATINGS
(25°C unless otherwise specified)

Storage Temperature	-40°C to +125°C
Operating Temperature	-30°C to +100°C
Lead Soldering Temperature (1/16 inch (1.6mm) from case for 10 secs)	260°C

INPUT DIODE

Forward Current	50mA
Reverse Voltage	6V
Power Dissipation	70mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV_{CEO}	35V
Emitter-collector Voltage BV_{ECO}	6V
Power Dissipation	150mW

POWER DISSIPATION

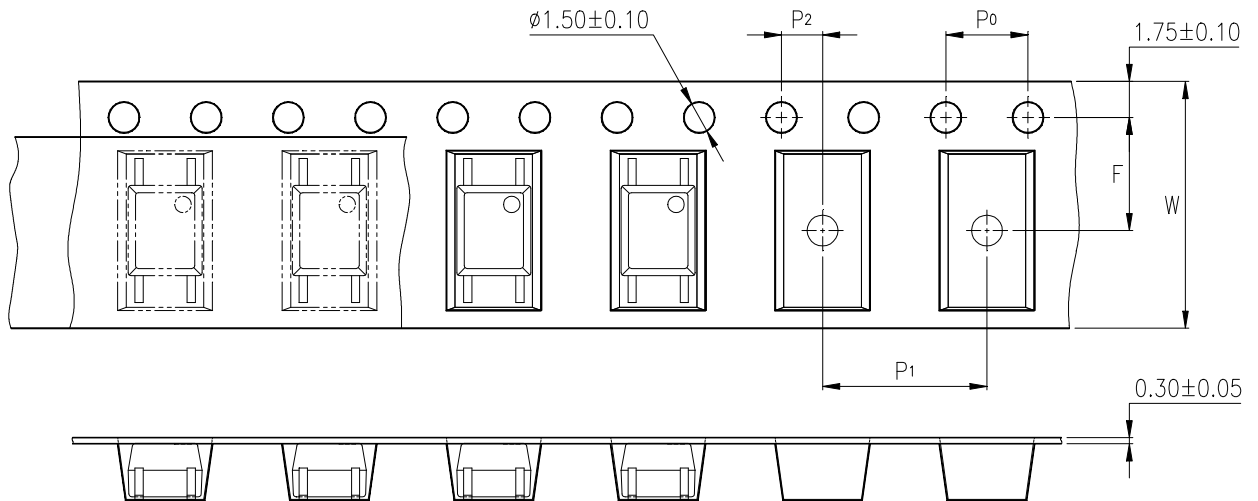
Total Power Dissipation	170mW
(derate linearly 2.26mW/°C above 25°C)	

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION	
Input	Forward Voltage (V_F)		1.2	1.4	V	$I_F = 20\text{mA}$	
	Reverse Voltage (V_R)	5			V	$I_R = 10\mu\text{A}$	
	Reverse Current (I_R)			10	μA	$V_R = 4\text{V}$	
Output	Collector-emitter Breakdown (BV_{CEO})	35			V	$I_C = 0.5\text{mA}$	
	Emitter-collector Breakdown (BV_{ECO})	6			V	$I_E = 0.1\text{mA}$	
	Collector-emitter Dark Current (I_{CEO})			100	nA	$V_{CE} = 20\text{V}$	
Coupled	Current Transfer Ratio (CTR)	50		600	%	$5\text{mA } I_F, 5\text{V } V_{CE}$	
	Optional CTR Grades:	IS357A	80		160	%	$5\text{mA } I_F, 5\text{V } V_{CE}$
		IS357B	130		260	%	$5\text{mA } I_F, 5\text{V } V_{CE}$
		IS357C	200		400	%	$5\text{mA } I_F, 5\text{V } V_{CE}$
		IS357D	300		600	%	$5\text{mA } I_F, 5\text{V } V_{CE}$
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$			0.2	V	$20\text{mA } I_F, 1.0\text{mA } I_C$	
	Input to Output Isolation Voltage V_{ISO}	3750 5300			V_{RMS} V_{PK}	See note 1 See note 1	
Input-output Isolation Resistance R_{ISO}	5×10^{10}			Ω	$V_{IO} = 500\text{V}$ (note 1)		
Output Rise Time t_r		4	18	μs	$V_{CE} = 2\text{V}$,		
Output Fall Time t_f		3	18	μs	$I_C = 2\text{mA}, R_L = 100\Omega$		

Note 1 Measured with input leads shorted together and output leads shorted together.

TAPING DIMENSIONS



Description	Symbol	Dimensions in mm (inches)
Tape wide	W	12 ± 0.3 (.47)
Pitch of sprocket holes	P_0	4 ± 0.1 (.15)
Distance of compartment	F	5.5 ± 0.1 (.217)
	P_2	2 ± 0.1 (.079)
Distance of compartment to compartment	P_1	8 ± 0.1 (.315)

CHARACTERISTIC CURVES

Fig.1 Forward Current vs. Ambient Temperature

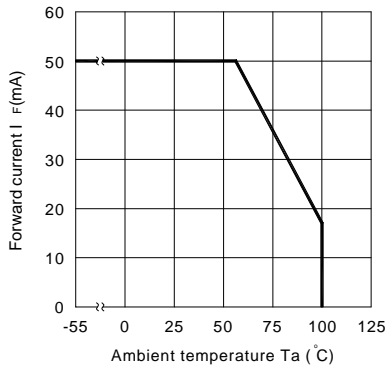


Fig.2 Collector Power Dissipation vs. Ambient Temperature

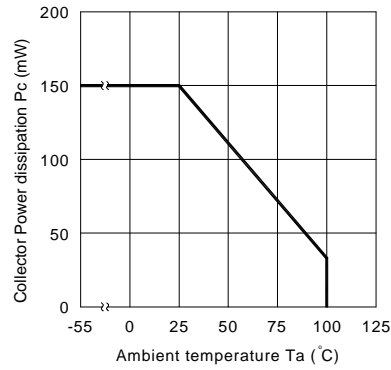


Fig.3 Collector-emitter Saturation Voltage vs. Forward Current

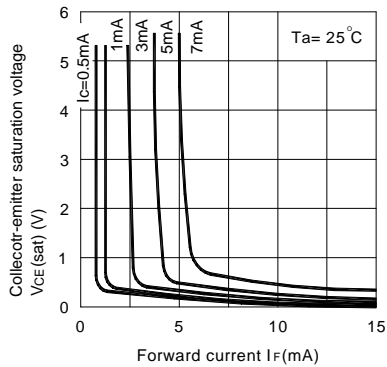


Fig.4 Forward Current vs. Forward Voltage

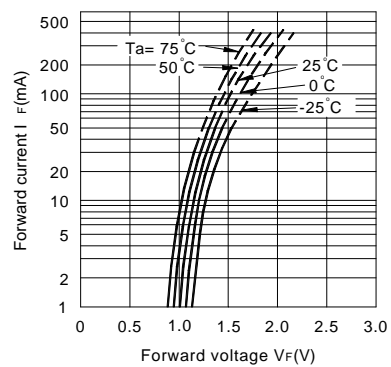


Fig.5 Current Transfer Ratio vs. Forward Current

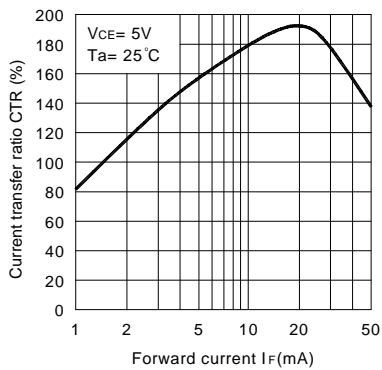
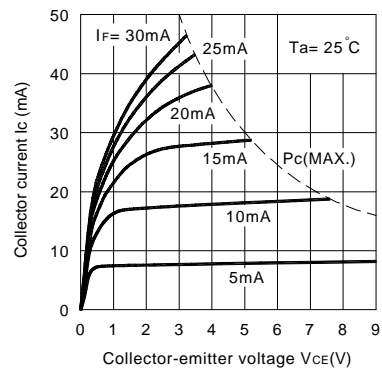


Fig.6 Collector Current vs. Collector-emitter Voltage



CHARACTERISTIC CURVES

Fig.7 Relative Current Transfer Ratio vs. Ambient Temperature

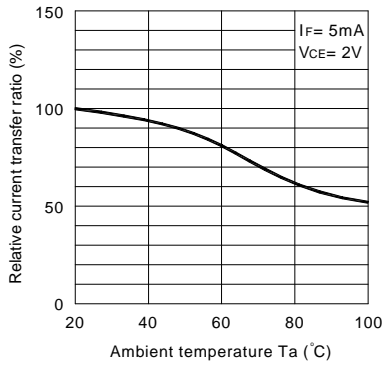


Fig.8 Collector-emitter Saturation Voltage vs. Ambient Temperature

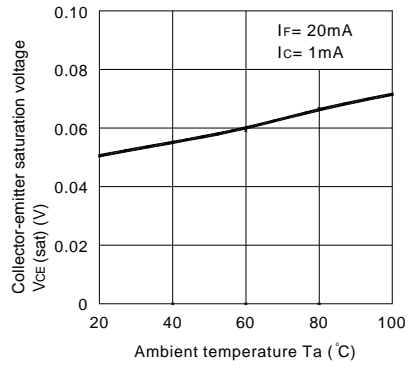


Fig.9 Collector Dark Current vs. Ambient Temperature

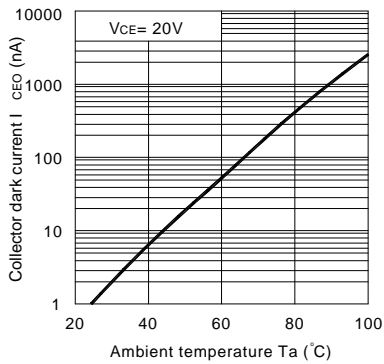


Fig.10 Response Time vs. Load Resistance

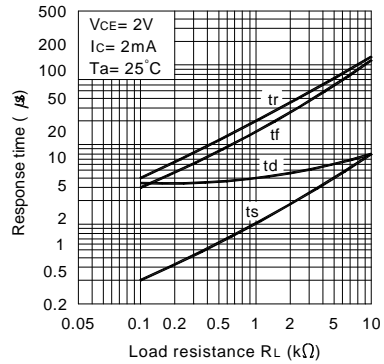
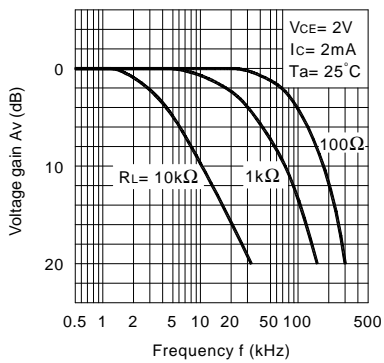
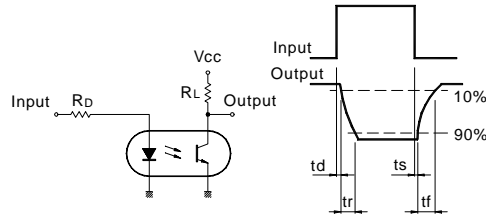


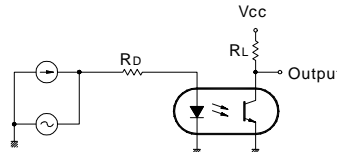
Fig.11 Frequency Response



Test Circuit for Response Time

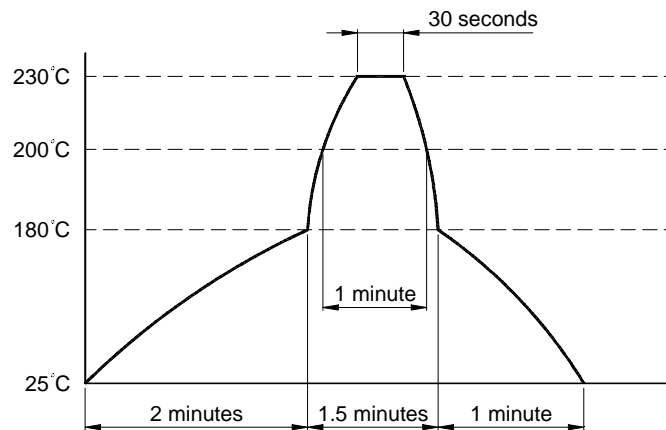


Test Circuit for Frequency Response



TEMPERATURE PROFILE OF SOLDERING REFLOW

- (1) One time soldering reflow is recommended within the condition of temperature and time profile shown below.



- (2) When using another soldering method such as infrared ray lamp, the temperature may rise partially in the mold of the device. Keep the temperature on the package of the device within the condition of above (1).